

SANYO Semiconductors **DATA SHEET**

2SK2628LS-

N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- · Low ON-resistance.
- · Low Qg.
- · Ultrahigh-speed switching.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	ID		6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	24	Α
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C	35	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		98	mJ
Avalanche Current *2	IAV		6	Α

^{*1} VDD=50V, L=5mH, IAV=6A

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =600V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	3.5		5.5	V

Marking: K2628 Continued on next page.

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^{*2} L≤5mH, single pulse

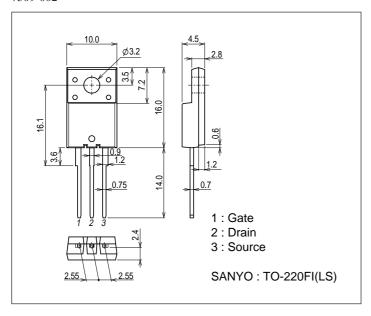
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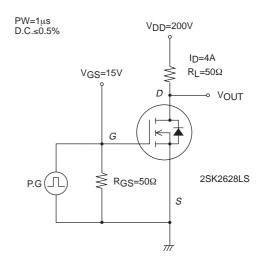
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =4A	2.0	4.0		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =2A, V _G S=15V		0.9	1.1	Ω
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		1050		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		320		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		180		pF
Total Gate Charge	Qg	V _{DS} =200V, I _D =6A, V _{GS} =10V		30		nC
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		23		ns
Rise Time	t _r	See specified Test Circuit.		35		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		90		ns
Fall Time	tf	See specified Test Circuit.		35		ns
Diode Forward Voltage	V _{SD}	I _S =6A, V _{GS} =0V		0.85	1.2	V

Package Dimensions

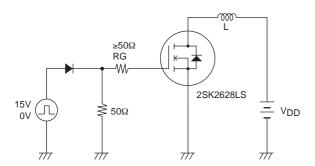
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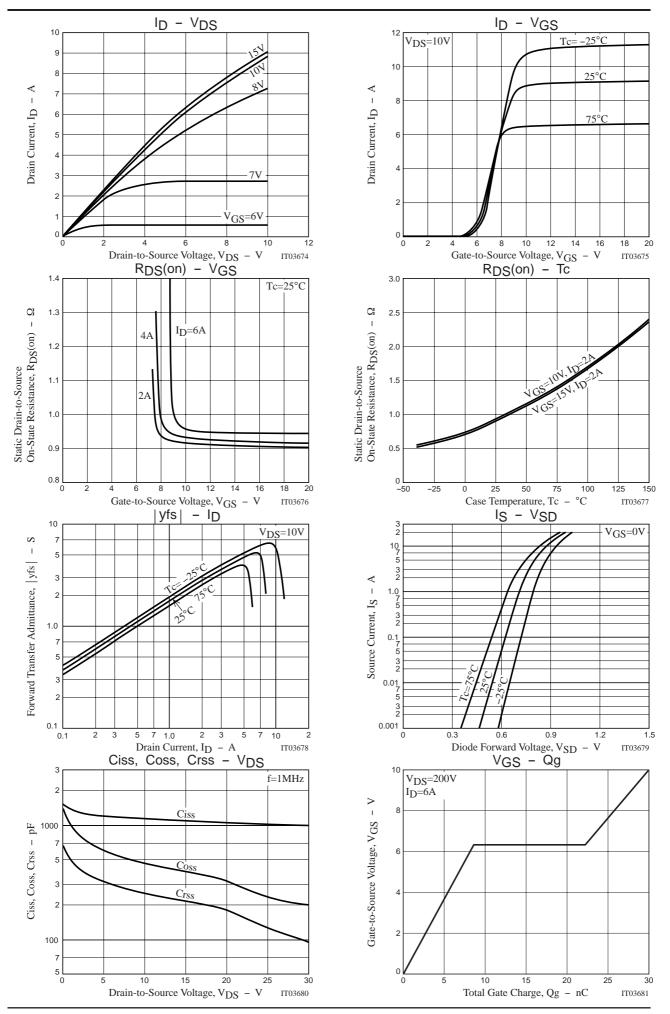


Switching Time Test Circuit

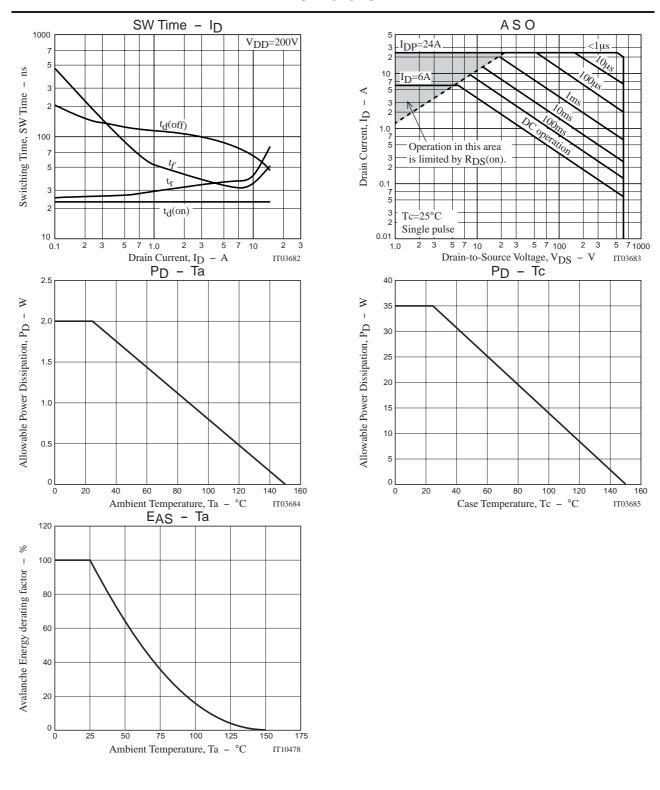


Avalanche Resistance Test Circuit





2SK2628LS



Note on usage : Since the 2SK2628LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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